Dual DPDT Ultra-Low R_{ON} Switch

The NLAS3699B is a dual independent ultra–low R_{ON} DPDT analog switch. This device is designed for low operating voltage, high current switching of speaker output for cell phone applications. It can switch a balanced stereo output. The NLAS3699B can handle a balanced microphone/speaker/ring—tone generator in a monophone mode. The device contains a break—before—make feature.

Features

• Single Supply Operation

1.65 to 4.5 V V_{CC}

Function Directly from LiON Battery

- Maximum Breakdown Voltage: 5.5 V
- Tiny 3 x 3 mm QFN Pb–Free Package Meet JEDEC MO–220 Specifications
- Low Static Power
- This is a Pb-Free Device*

Typical Applications

- Cell Phone Speaker/Microphone Switching
- Ringtone–Chip/Amplifier Switching
- Four Unbalanced (Single–Ended) Switches
- Stereo Balanced (Push-Pull) Switching

Important Information

• ESD Protection:

HBM (Human Body Model) > 8000 V MM (Machine Model) > 400 V

- Continuous Current Rating Through each Switch ±300 mA
- Conforms to: JEDEC MO-220, Issue H, Variation VEED-6
- Pin for Pin Compatible with STG3699



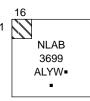
ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS



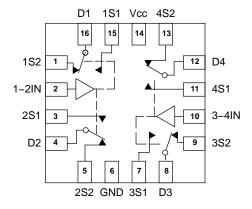
QFN-16 CASE 485AE



= Assembly Location

L = Wafer Lot Y = Year W = Work Week ■ = Pb-Free Package

(Note: Microdot may be in either location)



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 9 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

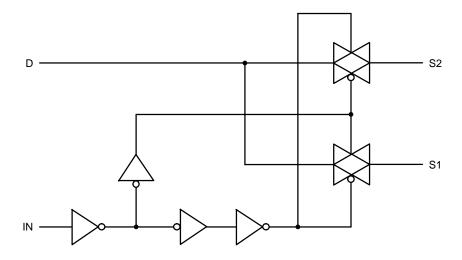


Figure 1. Input Equivalent Circuit

PIN DESCRIPTION

QFN PIN #	Symbol	Name and Function		
1, 3, 5, 7, 9, 11, 13, 15	1S1 to 4S1, 1S2 to 4S2	Independent Channels		
2, 10	1-2IN, 3-4IN	Controls		
4, 8, 12, 16	D1 to D4	Common Channels		
6	GND	Ground (V)		
14	V _{CC}	Positive Supply Voltage		

TRUTH TABLE

IN	S 1	S2		
Н	ON OFF(*)			
L	OFF(*)	ON		

^{*}High impedance.

MAXIMUM RATINGS

Symbol	Parameter	Va	Unit		
V _{CC}	Positive DC Supply Voltage	-0.5 to	o +5.5	V	
V _{IS}	Analog Input Voltage (V _{NO} , V _{NC} , or V _{COM})	-0.5 ≤ \	$I_{IS} \leq V_{CC}$	V	
V _{IN}	Digital Select Input Voltage	$-0.5 \le V_1 \le +5.5$		V	
I _{anl1}	Continuous DC Current from COM to NC/NO	±3	300	mA	
I _{anl-pk 1}	Peak Current from COM to NC/NO, 10 duty cycle (Note 1)	±500		mA	
I _{clmp}	Continuous DC Current into COM/NO/NC with respect to V	±100		mA	
t _r , t _f	Input Rise or Fall Time, SELECT	$V_{CC} = 1.6 \text{ V} - 2.7 \text{ V}$ $V_{CC} = 3.0 \text{ V} - 4.5 \text{ V}$	0 0	20 10	ns/V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Defined as 10% ON, 90% off duty cycle.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	1.65	4.5	V
V _{IN}	Digital Select Input Voltage	GND	V_{CC}	V
V _{IS}	Analog Input Voltage (NC, NO, COM)	GND	V_{CC}	V
T _A	Operating Temperature Range	-40	+85	°C
t _r , t _f	Input Rise or Fall Time, SELECT $V_{CC} = 1.0$ $V_{CC} = 3.0$	6 V – 2.7 V 0 0 V – 4.5 V 0	20 10	ns/V

DC CHARACTERISTICS - Digital Section (Voltages Referenced to GND)

				Guaranteed Limit		
Symbol	Parameter	Condition	V _{CC}	-40°C to 25°C	<85°C	Unit
V _{IH}	Minimum High-Level Input		1.8	1.2	1.2	V
	Voltage, Select Inputs		2.5	1.7	1.7	
			3.6	2.2	2.2	
			4.3	2.6	2.6	
V _{IL}	Maximum Low-Level Input		1.8	0.4	0.4	V
	Voltage, Select Inputs		2.5	0.5	0.5	
			3.6	0.7	0.7	
			4.3	0.9	0.9	
I _{IN}	Maximum Input Leakage Current, Select Inputs	$V_{IN} = V_{CC}$ or GND	4.3	±0.1	±1.0	μΑ
I _{OFF}	Power Off Leakage Current	V _{IN} = V _{CC} or GND	0	±0.5	± 2.0	μΑ
Icc	Maximum Quiescent Supply Current (Note 2)	Select and V _{IS} = V _{CC} or GND	1.65 to 4.5	±1.0	± 2.0	μΑ

DC ELECTRICAL CHARACTERISTICS - Analog Section

				Guara	inteed Ma	aximum	Limit	
				-40°C to 25°C <85°C		5°C		
Symbol	Parameter	Condition	V _{CC}	Min	Max	Min	Max	Unit
R _{ON}	NC/NO On–Resistance (Note 2)	$\begin{split} &V_{IN} \leq V_{IL} \text{ or } V_{IN} \geq V_{IH} \\ &V_{IS} = \text{GND to } V_{CC} \\ &I_{IN}I \leq 100 \text{ mA} \end{split}$	2.5 3.0 4.3		0.65 0.6 0.55		0.75 0.75 0.70	Ω
R _{FLAT}	NC/NO On–Resistance Flatness (Notes 2, 4)	I _{COM} = 100 mA V _{IS} = 0 to V _{CC}	2.5 3.0 4.3		0.15 0.15 0.15		0.15 0.15 0.15	Ω
ΔR _{ON}	On–Resistance Match Between Channels (Notes 2 and 3)	$V_{IS} = 1.3 \text{ V;} \\ I_{COM} = 100 \text{ mA} \\ V_{IS} = 1.5 \text{ V;} \\ I_{COM} = 100 \text{ mA} \\ V_{IS} = 2.2 \text{ V;} \\ I_{COM} = 100 \text{ mA} \\ $	2.5 3.0 4.3		0.06 0.05 0.05		0.06 0.05 0.05	Ω
I _{NC(OFF)} I _{NO(OFF)}	NC or NO Off Leakage Current (Note 2)	$\begin{aligned} V_{IN} &= V_{IL} \text{ or } V_{IH} \\ V_{NO} \text{ or } V_{NC} &= 0.3 \text{ V} \\ V_{COM} &= 4.0 \text{ V} \end{aligned}$	4.3	-10	10	-100	100	nA
I _{COM(ON)}	COM ON Leakage Current (Note 2)	$\begin{split} &V_{IN} = V_{IL} \text{ or } V_{IH} \\ &V_{NO} \text{ 0.3 V or 4.0 V with} \\ &V_{NC} \text{ floating or} \\ &V_{NC} \text{ 0.3 V or 4.0 V with} \\ &V_{NO} \text{ floating} \\ &V_{COM} = \text{ 0.3 V or 4.0 V} \end{split}$	4.3	-10	10	-100	100	nA

Guaranteed by design. Resistance measurements do not include test circuit or package resistance.
 ΔR_{ON =} R_{ON(MAX)} – R_{ON(MIN)} between nS1 or nS2.
 Flatness is defined as the difference between the maximum and minimum value of on–resistance as measured over the specified analog signal ranges.

AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0 \text{ ns}$)

					Guaranteed Maximum Limit					
			V _{CC}	V _{IS}	-40	0°C to 2	25°C	<8	5°C	
Symbol	Parameter	Test Conditions	(V)	(V)	Min	Тур*	Max	Min	Max	Unit
t _{ON}	Turn-On Time	$R_L = 50 \Omega$, $C_L = 35 pF$ (Figures 3 and 4)	2.3 – 4.5	1.5			50		60	ns
t _{OFF}	Turn-Off Time	$R_L = 50 \Omega$, $C_L = 35 pF$ (Figures 3 and 4)	2.3 – 4.5	1.5			30		40	ns
t _{BBM}	Minimum Break-Before-Make Time	$\begin{aligned} & \text{V}_{\text{IS}} = 3.0 \\ & \text{R}_{\text{L}} = 50 \ \Omega, \ \text{C}_{\text{L}} = 35 \ \text{pF} \\ & \text{(Figure 2)} \end{aligned}$	3.0	1.5	2	15				ns

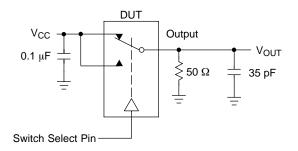
		Typical @ 25, V _{CC} = 4.5 V	
C _{IN}	Control Pin Input Capacitance	7.0	pF
C _{SN}	SN Port Capacitance	72	pF
C _D	D Port Capacitance When Switch is Enabled	230	pF

^{*}Typical Characteristics are at 25°C.

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

			V _{CC}	25°C	
Symbol	Parameter	Condition	(V)	Typical	Unit
BW	Maximum On–Channel –3dB Bandwidth or Minimum Frequency Response (Figure 12)	V _{IN} centered between V _{CC} and GND (Figure 5)	1.65 – 4.5	20	MHz
V _{ONL}	Maximum Feed-through On Loss	V_{IN} = 0 dBm @ 100 kHz to 50 MHz V_{IN} centered between V_{CC} and GND (Figure 5)	1.65 – 4.5	-0.06	dB
V _{ISO}	Off-Channel Isolation (Figure 13)	$f = 100 \text{ kHz}$; $V_{IS} = 1 \text{ V RMS}$; $C_L = 5 \text{ pF}$ V_{IN} centered between V_{CC} and GND(Figure 5)	1.65 – 4.5	-62	dB
Q	Charge Injection Select Input to Common I/O (Figure 8)	$V_{IN} = V_{CC \text{ to}}$ GND, $R_{IS} = 0 \Omega$, $C_L = 1 \text{ nF}$ $Q = C_L \times \Delta V_{OUT}$ (Figure 6)	1.65 – 4.5	50	pC
THD	Total Harmonic Distortion THD + Noise (Figure 7)	F_{IS} = 20 Hz to 20 kHz, R_L = R_{gen} = 600 Ω , C_L = 50 pF V_{IS} = 2 V_{PP}	4.5	0.01	%
VCT	Channel-to-Channel Crosstalk	f = 100 kHz; V_{IS} = 1 V RMS, C_L = 5 pF, R_L = 50 Ω V_{IN} centered between V_{CC} and GND (Figure 5)	1.65 – 4.5	-62	dB

^{5.} Off-Channel Isolation = 20log10 (Vcom/Vno), Vcom = output, Vno = input to off switch.



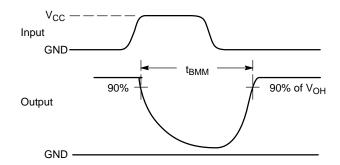
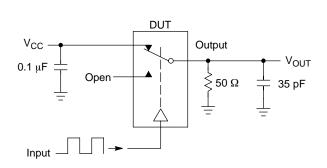


Figure 2. t_{BBM} (Time Break-Before-Make)



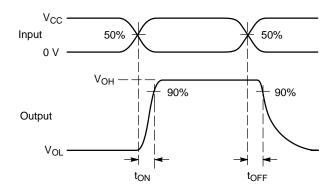
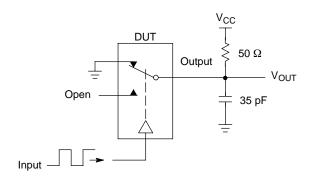


Figure 3. t_{ON}/t_{OFF}



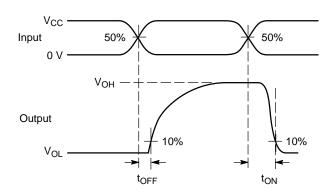
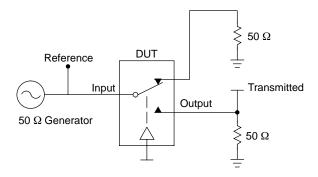


Figure 4. t_{ON}/t_{OFF}



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO} , Bandwidth and V_{ONL} are independent of the input signal direction.

$$\begin{split} &V_{ISO} = \text{Off Channel Isolation} = 20 \text{ Log} \left(\frac{V_{OUT}}{V_{IN}} \right) \text{ } \text{ for } V_{IN} \text{ at } 100 \text{ kHz} \\ &V_{ONL} = \text{On Channel Loss} = 20 \text{ Log} \left(\frac{V_{OUT}}{V_{IN}} \right) \text{ } \text{ for } V_{IN} \text{ at } 100 \text{ kHz to } 50 \text{ MHz} \end{split}$$

Bandwidth (BW) = the frequency 3 dB below V_{ONL}

 V_{CT} = Use V_{ISO} setup and test to all other switch analog input/outputs terminated with 50 Ω

Figure 5. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V_{ONL}

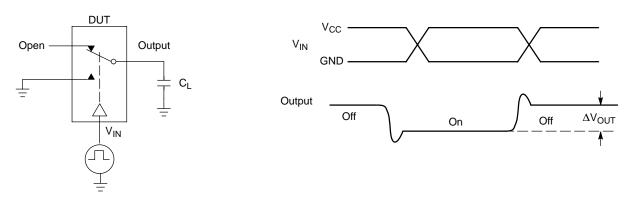


Figure 6. Charge Injection: (Q)

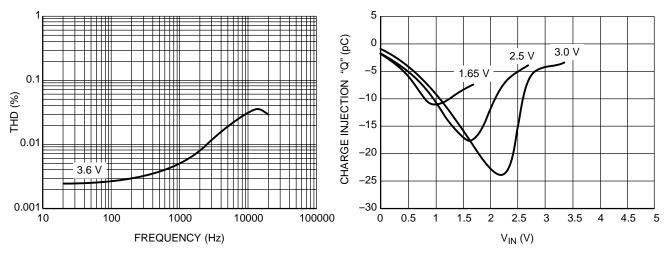


Figure 7. Total Harmonic Distortion Plus Noise Versus Frequency

Figure 8. Charge Injection versus Vis

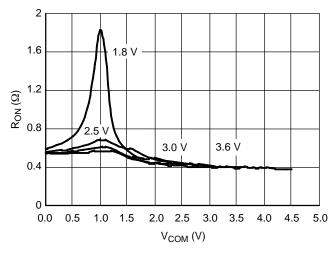


Figure 9. On-Resistance vs. COM Voltage

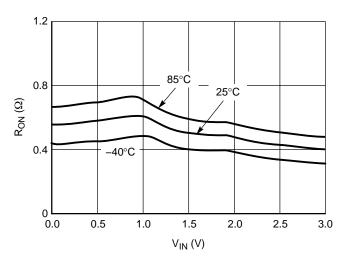


Figure 10. R_{ON} vs. V_{IN} vs. Temperature @ V_{CC} = 3.0 V

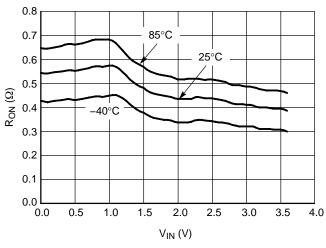


Figure 11. R_{ON} vs. V_{IN} vs. Temperature @ V_{CC} = 3.6 V

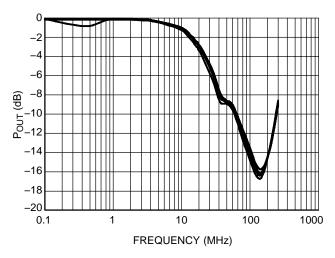


Figure 12. Bandwidth vs. Frequency @ V_{CC} = 1.65 V to 3.6 V

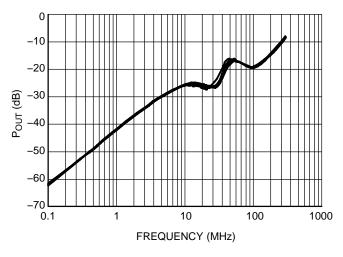


Figure 13. Off-Isolation vs. Frequency $@V_{CC} = 1.65 \text{ V}$ to 3.6 V

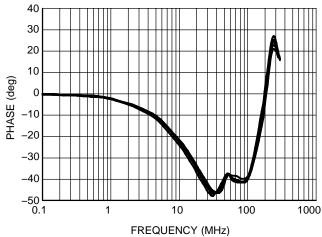


Figure 14. Phase Angle vs. Frequency @ V_{CC} = 1.65 V to 3.6 V

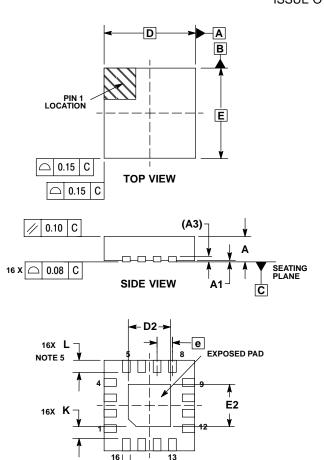
DEVICE ORDERING INFORMATION

		Devi	ce Nomenc	lature				
Device Order Number	Circuit Indicator	Technology	Device Function	Package Suffix	Tape & Reel Suffix	Package Type	Tape & Reel Size [†]	
NLAS3699BMN1R2G	NL	AS	3699B	MN1	R2G	QFN (Pb-Free)	3000 Unit / Reel	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

QFN-16 (3 x 3 x 0.85 mm) CASE 485AE-01 **ISSUE O**



BOTTOM VIEW

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. DIMENSION b APPLIES TO PLATED
- TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
- COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
- OUTLINE MEETS JEDEC DIMENSIONS PER MO–220, VARIATION VEED–6.

	MILLIMETERS					
DIM	MIN	NOM	MAX			
Α	0.800	0.900	1.000			
A1	0.000	0.025	0.050			
A3		0.200 RE	F			
b	0.180	0.180 0.250 0.				
D		3.00 BS	С			
D2	1.250	1.40	1.550			
E		3.00 BS	С			
E2	1.250	1.40	1.550			
е	0.500 BSC					
K	K 0.200					
L	0.300	0.400	0.500			

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С A B

С 0.05

NOTE 3

0.10

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